$LED1200\text{-}35M32 \quad \text{Stem type LED with high output power}$

LED1200-35M32 is an InGaAsP LED mounted on a TO-18 stem with a spherical glass lens being designed for high output power uses. On forward bias, it emits a spectral band of radiation, which peaks at 1200nm.

♦ Features

- 1) High radiated intensity
- 2) High Reliability

◆Specifications

1) Product Name NIR LED Lamp 2) Type No. LED1200-35M32

3) Chip Spec.

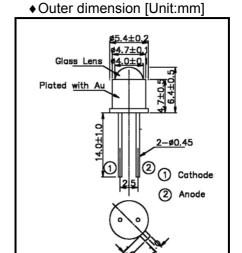
(1) Material InGaAs/InP(2) Peak Wavelength 1200 nm

4) Package

(1) Type TO-18 stem

(2) Lens Spherical glass lens

(3) Cap Gold plated



♦Absolute Maximum Ratings

Item	Symbol	Maximum Rated Value	Unit	Ambient Temperature	
Power Dissipation	Po	120	mW	Ta = 25 °C	
Forward Current	lF	100	mΑ	Ta = 25 °C	
Pulse Forward Current	lfp	1000	mA	Ta = 25 °C	
Reverse Voltage	Vr	3	V	Ta = 25 °C	
Operating Temperature	Topr	-20 ~ +90	°C		
Storage Temperature	Тsтg	-30 ~ +100	°C		
Soldering Temperature	TsoL	260	°C		

 $[\]pm$ Pulse Forward Current condition: Duty = 1% and Pulse Width = 10 μ s.

◆ Electro-Optical Characteristics

Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	VF	IF = 20 mA		0.8	1.3	V
Reverse Current	lr	VR = 3 V			10	uA
Total Radiated Power	Po	IF = 20 mA	0.8	1.8		mW
Peak Wavelength	λP	IF = 20 mA	1150	1200	1250	nm
Half Width	Δλ	IF = 20 mA		100		nm
Viewing Half Angle	θ 1/2	IF = 20 mA		±15		deg.
Rise Time	tr	IF = 20 mA		10		ns
Fall Time	tf	IF = 20 mA		10		ns

‡Radiated Power is measured by Ando Optical Multi Meter AQ2140 & AQ2742

[‡]Soldering condition: Soldering condition must be completed within 3 seconds at 260°C